

Absolute Maximum Ratings

(Ta=25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-source(GND) voltage ⁽¹⁾	V _{DSS}	400	V
Drain-Gate Voltage (R _{GS} =1MΩ)	V _{DGR}	400	V
Gate-source (GND) Voltage	V _{GS}	±30	V
Drain current pulsed ⁽²⁾	I _{DM}	18.4	ADC
Single pulsed avalanche energy ⁽³⁾	E _{AS}	360	mJ
Avalanche current ⁽⁴⁾	I _{AS}	20	A
Continuous drain current (T _C = 25°C)	I _D	4.6	ADC
Continuous drain current (T _C =100°C)	I _D	2.9	ADC
Supply voltage	V _{CC}	40	V
Analog input voltage range	V _{sync}	−0.3 to 13V	V
	V _{FB}	−0.3 to V _{CC}	V
Total Power Dissipation	P _D (Watt H/S)	42	W
	Derating	0.33	W/°C
Operating temperature	T _{OPR}	−25 to +85	°C
Thermal Resistance	R _{thjc}	2.98	°C/W
Storage Temperature	T _{STG}	−55 to +150	°C

Notes:

1. T_j = 25°C to 150°C
2. Repetitive rating: Pulse width limited by maximum junction temperature
3. L = 30mH, V_{DD} = 50V, R_G = 25Ω, starting T_j = 25°C
4. L = 13uH, starting T_j = 25°C

Electrical Characteristics (SFET part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV _{DSS}	V _{GS} = 0V, I _D = 50μA	400	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} = Max, Rating, V _{GS} = 0V	-	-	200	μA
		V _{DS} = 0.8*Max., Rating V _{GS} = 0V, T _a = 125°C	-	-	300	μA
Static drain-source on resistance ^(note)	R _{DS(ON)}	V _{GS} = 10V, I _D = 2.3A	-	0.9	1.1	Ω
Forward transconductance ^(note)	g _{fs}	V _{DS} = 50V, I _D = 2.3A	6.0	-	-	S
Input capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	-	710	-	pF
Output capacitance	C _{oss}		-	90	-	
Reverse transfer capacitance	C _{rss}		-	10	-	
Turn on delay time	t _{d(on)}	V _{DD} = 0.5BV _{DSS} , I _D = 7.0A (MOSFET switching time are essentially independent of operating temperature)	-	15	-	nS
Rise time	t _r		-	55	-	
Turn off delay time	t _{d(off)}		-	55	-	
Fall time	t _f		-	50	-	
Total gate charge (gate-source+gate-drain)	Q _g	V _{GS} = 10V, I _D = 7.0A, V _{DS} = 0.5B V _{DSS} (MOSFET Switching time are Essentially independent of operating temperature)	-	20	26	nC
Gate source charge	Q _{gs}		-	4.0	-	
Gate drain (Miller) charge	Q _{gd}		-	7.3	-	

Note:

1. Pulse test : Pulse width ≤ 300μS, duty ≤ 2%

2. $S = \frac{1}{R}$

Electrical Characteristics

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
UVLO SECTION						
Start Threshold Voltage	VSTART	VFB = GND	14	15	16	V
Stop Threshold Voltage	VSTOP	VFB = GND	8	9	10	V
SENSEFET SECTION						
Drain to PKG Breakdown voltage	BVpkg	60HZ AC, Ta = 25°C	3500	-	-	V
Drain to Source Breakdown voltage	BVdss	Ta = 25°C	400	-	-	V
Drain to Source Leakage current	Idss	Vdrain = 400V, Ta = 25°C	-	-	200	uA
OSCILLATOR SECTION						
Initial Frequency	FOSC	-	18	20	22	kHz
Voltage Stability	FSTABLE	12V ≤ Vcc ≤ 23V	0	1	3	%
Temperature Stability (note2)	ΔFOSC	-25°C ≤ Ta ≤ 85°C	0	±5	±10	%
Maximum Duty Cycle	DMAX	-	92	95	98	%
Minimum Duty Cycle	DMIN	-	-	-	0	%
FEEDBACK SECTION						
Feedback Source Current	IFB	VFB = GND	0.7	0.9	1.1	mA
Shutdown Feedback Voltage	VSD	Vfb ≥ 6.9V	6.9	7.5	8.1	V
Shutdown Delay Current	IDELAY	VFB = 5V	4	5	6	μA
PROTECTION SECTION						
Over Voltage Protection	VOVP	Vsync ≥ 11V	11	12	13	V
Over Current Latch Voltage (Note2)	VOCL	-	0.9	1.0	1.1	V
Thermal Shutdown Temp.	TSD	-	140	160	-	°C

Note:

1. These parameters is the current flowing in the Control IC.
2. These parameters, although guaranteed, are tested in EDS(wafer test) process.
3. These parameters indicate Inductor Current.

Electrical Characteristics (Continued)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Sync SECTION						
Normal Sync High Threshold Voltage	VNSH	V _{CC} = 16V, V _{fb} = 5V	4.0	4.6	5.2	V
Normal Sync Low Threshold Voltage	VNSL	V _{CC} = 16V, V _{fb} = 5V	2.3	2.6	2.9	V
Burst Sync High Threshold Voltage	VBSH	V _{CC} = 10.5V, V _{fb} = 0V	3.2	3.6	4.0	V
Burst Sync Low Threshold Voltage	VBSL	V _{CC} = 10.5V, V _{fb} = 0V	1.1	1.3	1.5	V
BURST MODE SECTION						
Burst mode Low Threshold Voltage	VBURL	V _{fb} = 0V	10.4	11.0	11.6	V
Burst mode High Threshold Voltage	VBURH	V _{fb} = 0V	11.4	12.0	12.6	V
Burst mode Enable Feedback Voltage	VBEN	V _{CC} = 10.5V	0.7	1.0	1.3	V
Burst mode Peak Current Limit	IBU_PK	V _{CC} = 10.5V	0.65	0.85	1.0	A
PRIMARY SIDE REGULATION SECTION						
Primary Regulation Threshold Voltage	V _{PR}	I _{fb} = 700uA, V _{fb} = 4V	32.0	32.5	33.0	V
Primary Regulation Transconductance	G _{PR}	-	2.0	2.6	-	mA/V
CURRENT LIMIT(SELF-PROTECTION)SECTION						
Peak Current Limit(Note3)	I _{PK}	-	4.4	5.0	5.6	A
TOTAL DEVICE SECTION						
Start Up Current	I _{START}	V _{fb} = GND, V _{CC} = 14V	-	0.1	0.2	mA
Operating supply current (Note1)	I _{OP}	V _{fb} = GND, V _{CC} = 16V	-	10	18	mA
	I _{OP(MIN)}	V _{fb} = GND, V _{CC} = 10V				
	I _{OP(MAX)}	V _{fb} = GND, V _{CC} = 28V				

Note:

1. These parameters is the current flowing in the Control IC.
2. These parameters, although guaranteed, are tested in EDS(wafer test) process.
3. These parameters indicate Inductor Current.

Typical Performance Characteristics

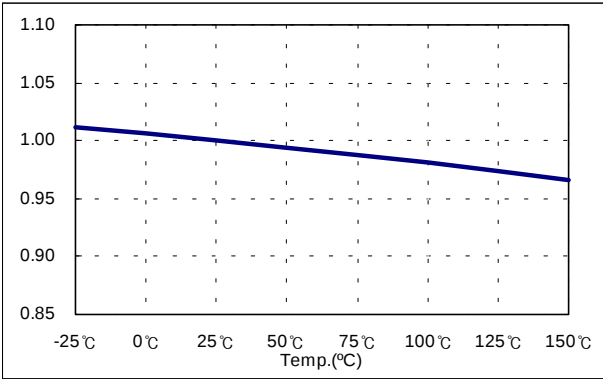


Figure 1. Start Voltage

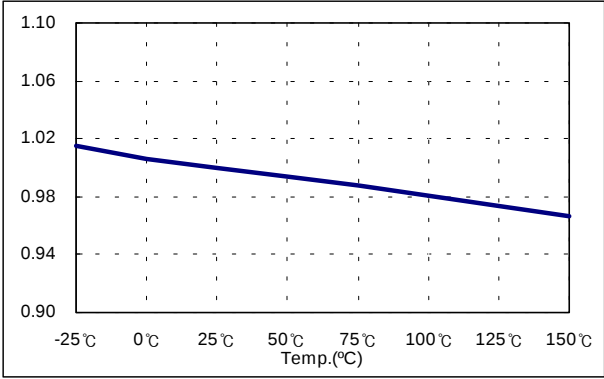


Figure 2. Stop Voltage

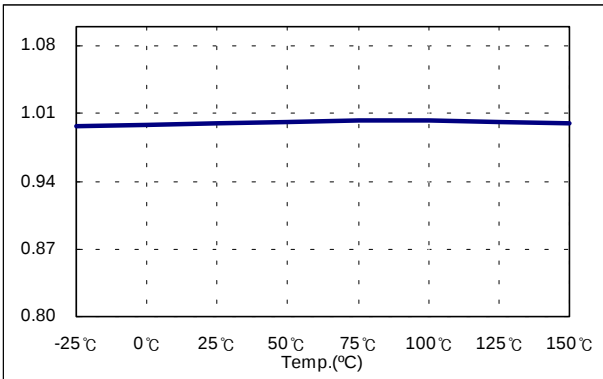


Figure 3. Stand by Current

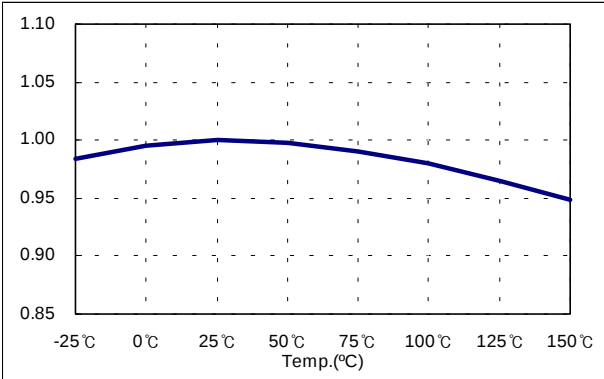


Figure 4. Operating Current

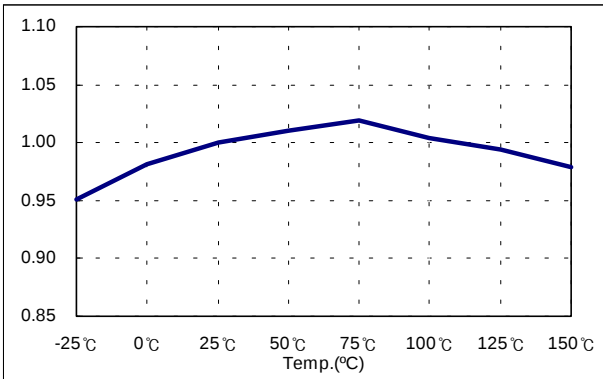


Figure 5. Initial Frequency

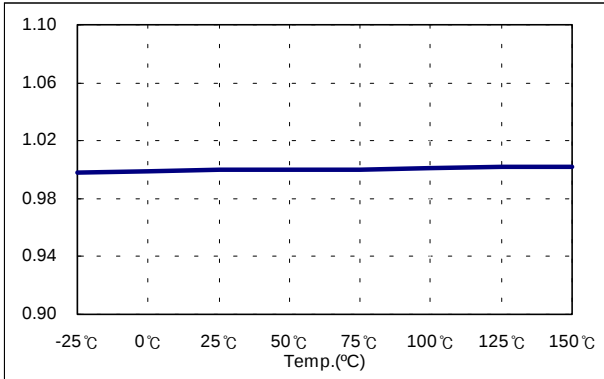


Figure 6. Maximum Duty

Typical Performance Characteristics (Continued)

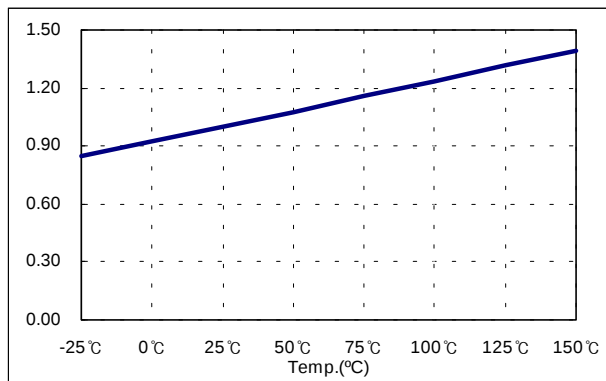


Figure 7. Feedback Offset Voltage

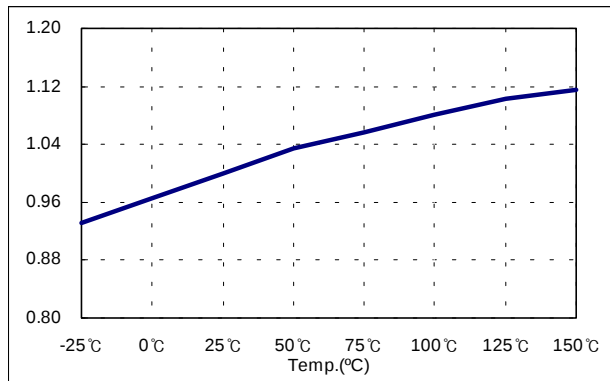


Figure 8. Feedback Source Current

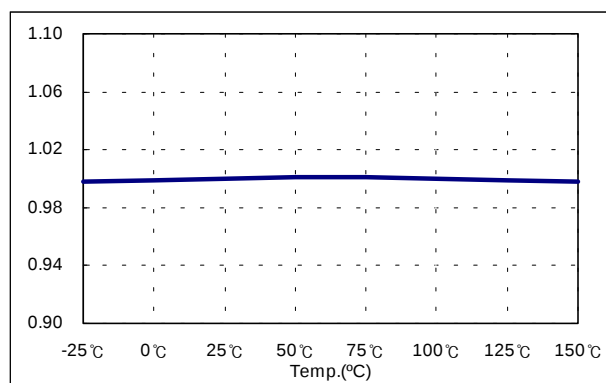


Figure 9. Over Voltage Protection

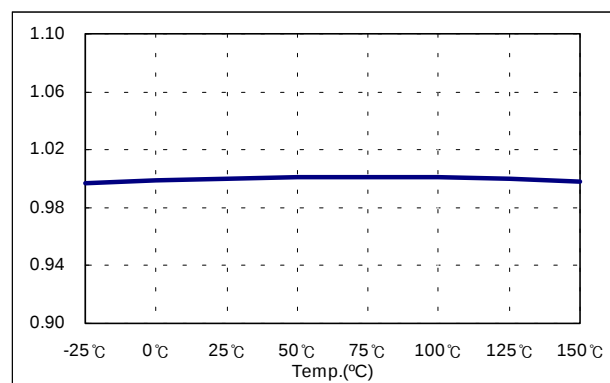


Figure 10. Shutdown Feedback Voltage

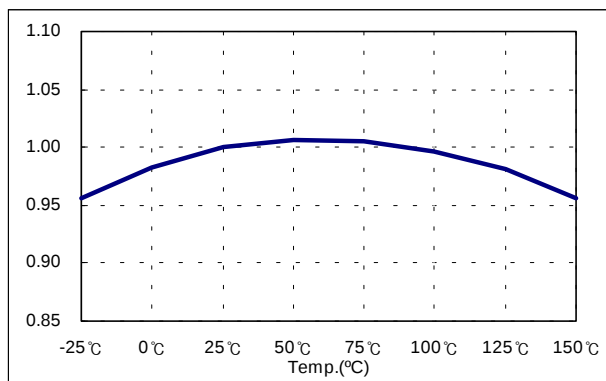


Figure 11. ShutDown Delay Current

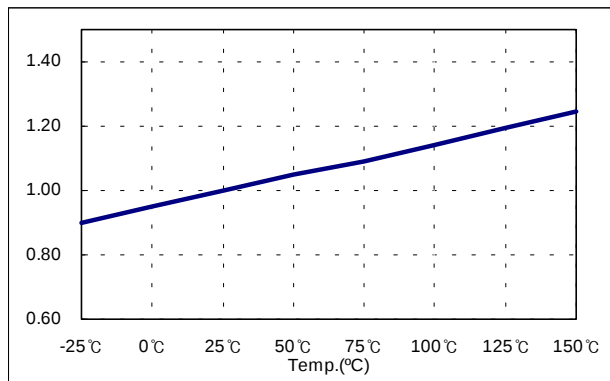


Figure 12. Burst Mode Enable Feedback Voltage

Typical Performance Characteristics (Continued)

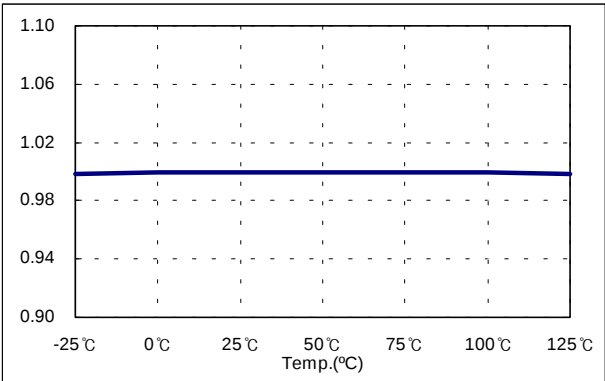


Figure 13. Burst Mode Low Threshold Voltage

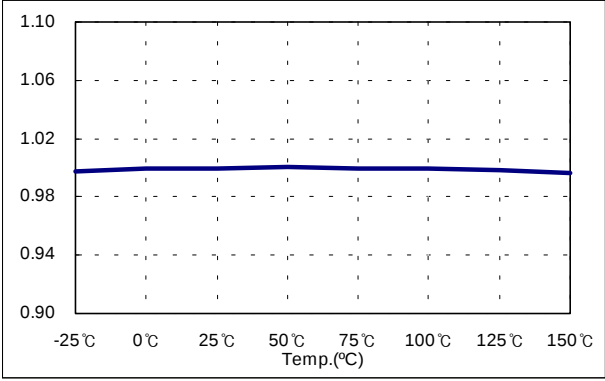


Figure 14. Burst Mode High Threshold Voltage

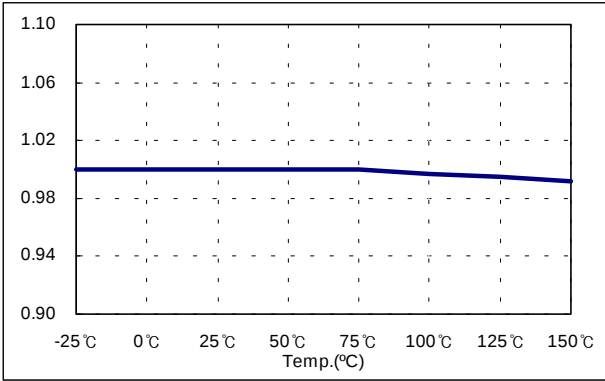


Figure 15. Burst Mode Sync. High Threshold Voltage

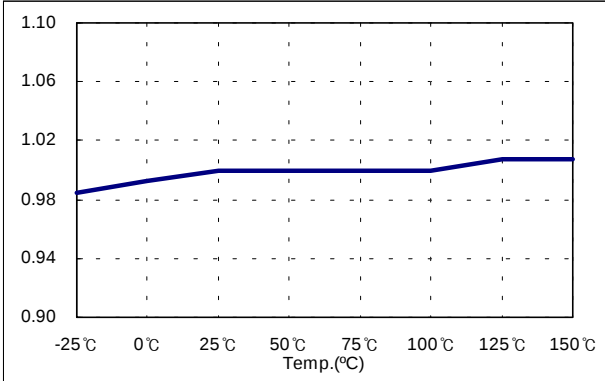


Figure 16. Burst Mode Sync. Low Threshold Voltage

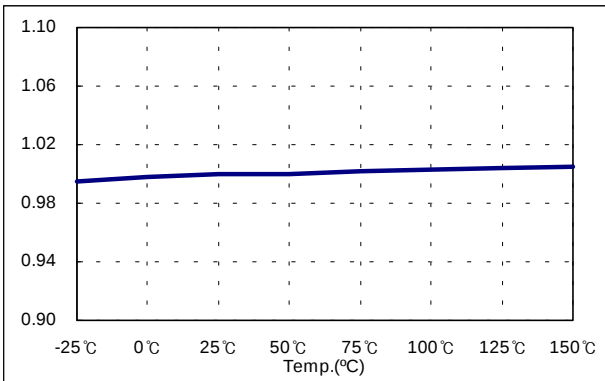


Figure 17. Primary Voltage

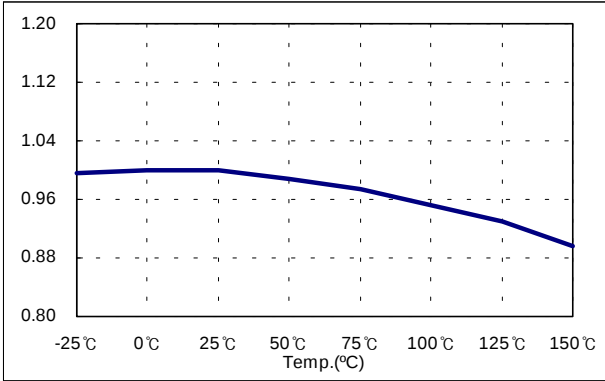


Figure 18. Primary Mode Gain

Typical Performance Characteristics (Continued)

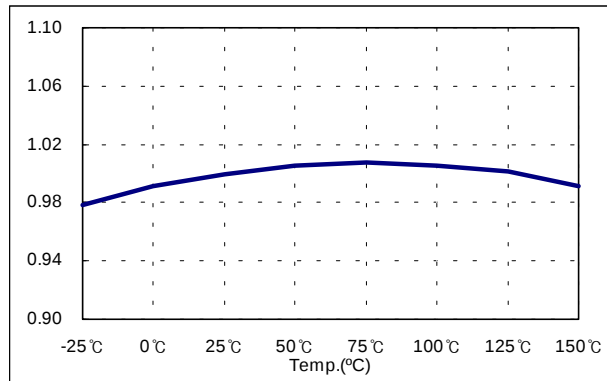


Figure 19. Peak Current Limit

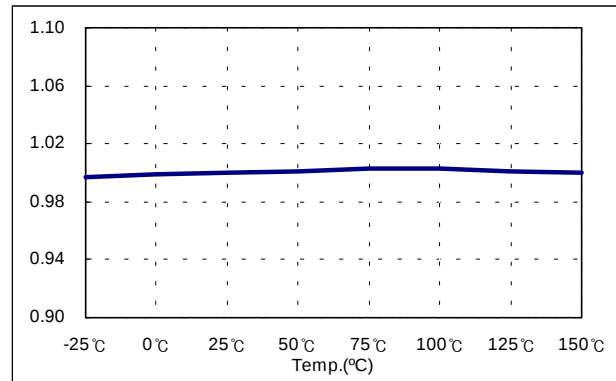


Figure 20. Burst Mode Peak Current Limit

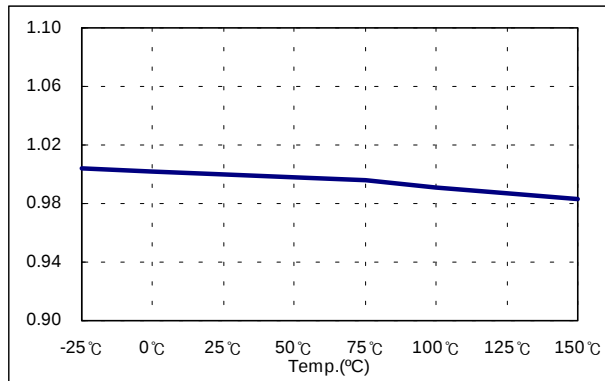


Figure 21. Normal Mode Sync. High Threshold Voltage

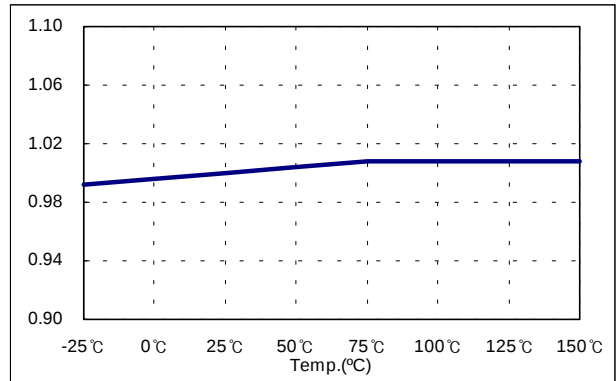


Figure 21. Normal Mode Sync. Low Threshold Voltage

Typical Performance Characteristics(MOSFET Part)

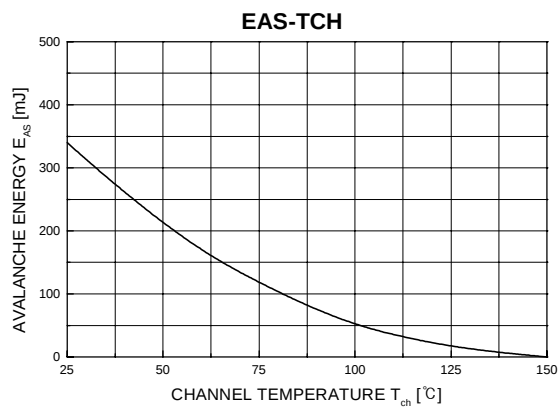


Figure 22. Temperature (T_C) vs. Eas Curve

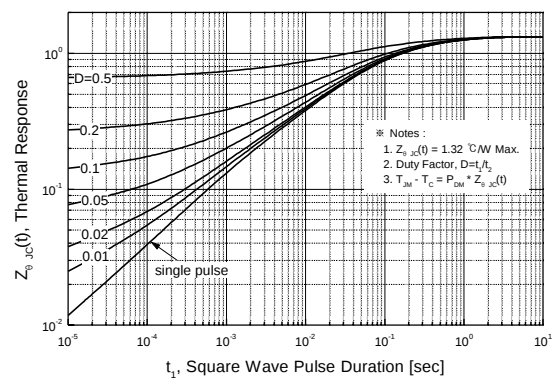
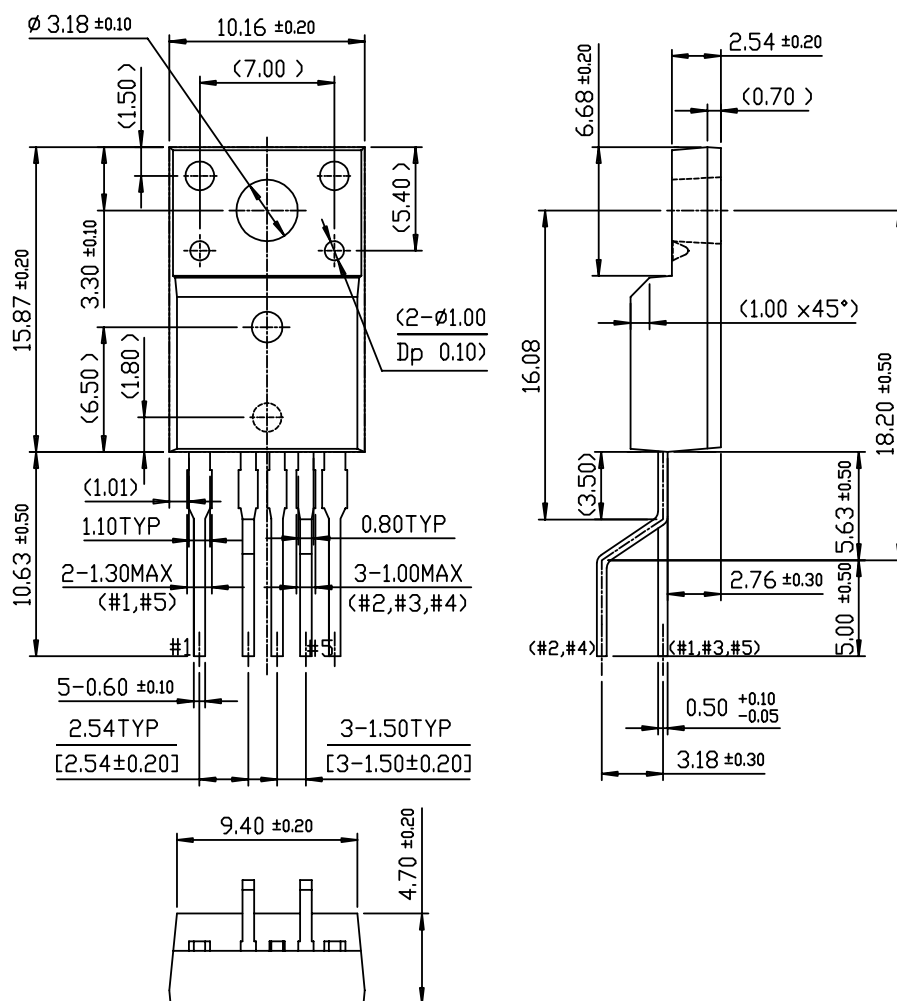


Figure 23. Transient Thermal Response Curve

Package Dimensions (Continued)

TO-220F-5L(Forming)



Ordering Information

Product Number	Package	Operating Temp.
KA5Q0740RT-TU	TO-220F-5L	-25°C to +85°C
KA5Q0740RT-YDTU	TO-220F-5L(Forming)	

TU : Non Forming Type

YDTU : Forming Type

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.